

(11) Publication number:

07249618 A

PATENT ABSTRACTS OF JAPAN

Generated Document.

(21) Application number: 06042182

(51) Intl. Cl.: H01L 21/31 H01L 21/318

(22) Application date: 14.03.94

(30) Priority:

(43) Date of application 26.09.95

(74) Representative:

(84) Designated contracting

states:

publication:

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(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

(57) Abstract:

PURPOSE: To provide a forming method of a silicon nitride film wherein the improvement of oxidation resistance and high speed of film formation are compatible with each other.

CONSTITUTION: A silicon nitride film is formed by a thermal CVD method using silane and ammonia as material gas, at a temperature lower

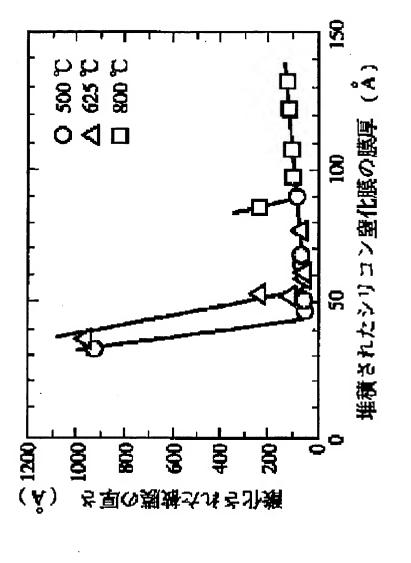
higher than or equal to 10Torr. In this than or equal to 630°C and a pressure instead of silane as the material gas, instead of ammonia as the material disilane and trisilane may be used case, higher order silane such as monomethylhydrazine and trimethylhydrazine may be used and hydrazine or derivative of hydrazine such as

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